



# Product data sheet

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MS8205A HF 🐼

Semiconductor Compiance

#### Description

The MS8205A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a

Battery protection or in other Switching application.

#### **General Features**

 $V_{DS}$  = 20V  $I_D$  = 5 A

 $R_{DS(ON)} < 23m\Omega @ V_{GS}=4.5V$ 

#### Application

Battery protection

Load switch

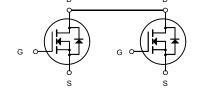
Uninterruptible power supply

#### Absolute Maximum Ratings@T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>GS</sub>	Gate-Source Voltage	<u>+</u> 10	V
ID@TA=25°C	Drain Current, V <sub>GS</sub> @ 4.5V <sup>3</sup>	5	А
Ідм	Pulsed Drain Current <sup>1</sup>	20	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation	1.25	W
Тята	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	a Maximum Thermal Resistance, Junction- ambient <sup>3</sup>		°C/W







Dual N-Channel MOSFET





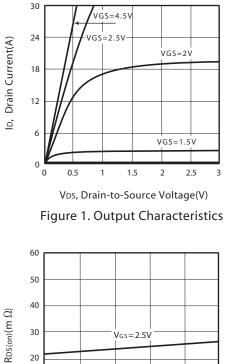
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## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CH/	ARACTERISTICS					
BVDSS	Drain-Source Breakdown Voltage	Vgs=0V , ID=250uA	20			V
IDSS	Zero Gate Voltage Drain Current	VDS=16V, VGS=0V			1	uA
lgss	Gate-Body Leakage Current	Vgs= ±10V , Vds=0V			±100	nA
ON CHA	RACTERISTICS	·				
VGS(th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.5	0.7	1.2	V
	Drain-Source On-State Resistance	Vgs=4.5V,Id=4A		20	23	m
D		Vgs=2.5V,Id=3A		25	28	m
RDS(ON)						
<b>g</b> <sub>FS</sub>	Forward Transconductance	VDS=10V,ID=5A		10		S
DYNAMI	C CHARACTERISTICS $^\circ$					
Ciss	Input Capacitance			800		pF
Coss	Output Capacitance	VDS=8V,VGS=0V f=1.0MHz		155		pF
Crss	Reverse Transfer Capacitance			125		pF
SWITCH	ING CHARACTERISTICS <sup>°</sup>					
td(on)	Turn-On Delay Time	V <sub>DD</sub> =10V		18.3		ns
tr	Rise Time			4.8		ns
td(off)	Turn-Off Delay Time	Vgs=10V		43.5		ns
tf	Fall Time	RGEN=60hm		20		ns
Qg	Total Gate Charge			11		nC
Qgs	Gate-Source Charge	VDs=10V,ID=3A, VGs=4.5V		2.2		nC
Qgd	Gate-Drain Charge	VGS=4.5V		2.5		nC
	OURCE DIODE CHARACTERISTIC		s			
ls	Maximum Continuous Drain-Source I				2	А
Vsd	Diode Forward Voltage <sup>b</sup>	Vgs=0V,Is=1.7A		0.79	1.2	V
b.Pulse T	Mounted on FR4 Board,t $\leq$ 10sec. Test:Pulse Width $\leq$ 300us, Duty Cycle $\leq$ teed by design, not subject to production					









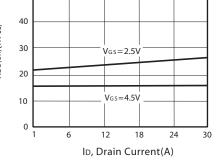
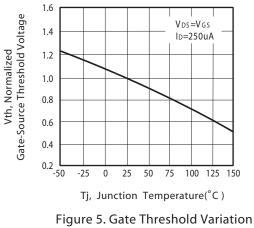


Figure 3. On-Resistance vs. Drain Current and Gate Voltage



with Temperature

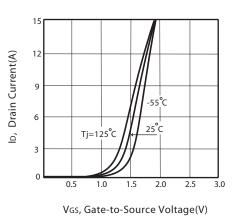


Figure 2. Transfer Characteristics

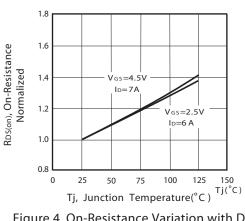
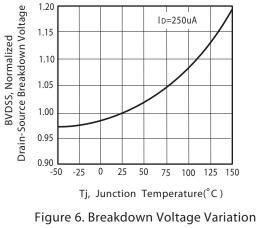


Figure 4. On-Resistance Variation with Drain Current and Temperature



with Temperature





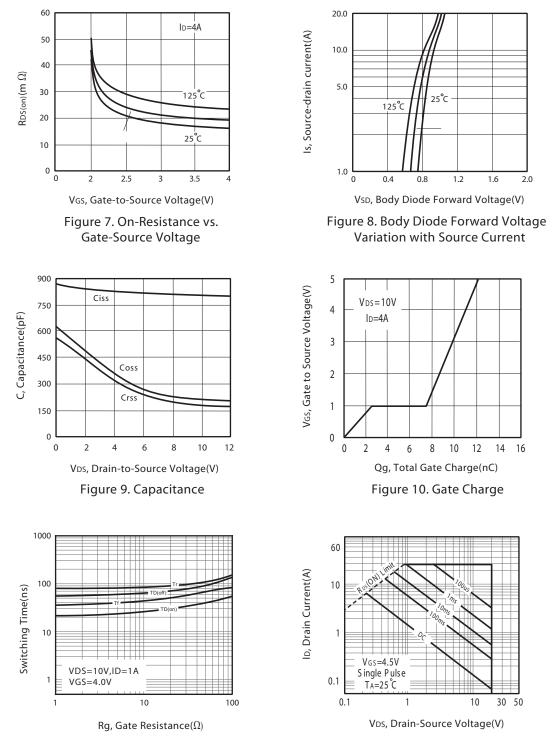


Figure 11. switching characteristics

Figure 12. Maximum Safe Operating Area





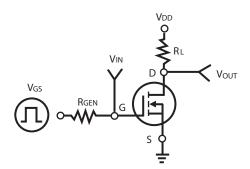


Figure 13. Switching Test Circuit

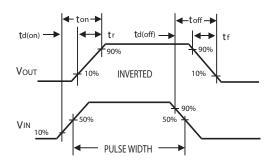
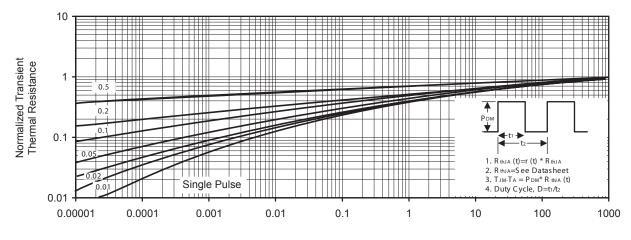


Figure 14. Switching Waveforms

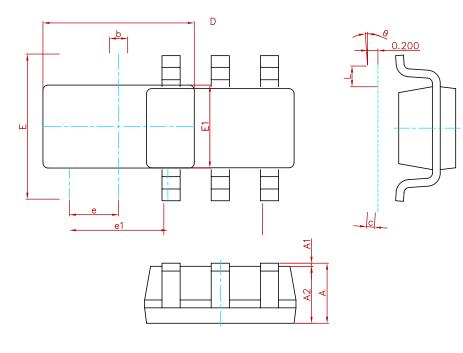


Square Wave Pulse Duration(sec) Normalized Thermal Transient Impedance Curve



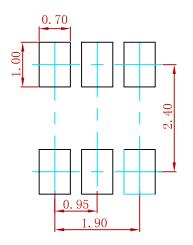


## PACKAGE MECHANICAL DATA



Symbol	Dimensions In	mensions In Millimeters		s In Inches
Symbol	Min.	Max.	Min.	Max.
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
е	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

## Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters. 2.General tolerance:± 0.05mm.

3. The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY
MS8205A	SOT-23-6L	3000





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